

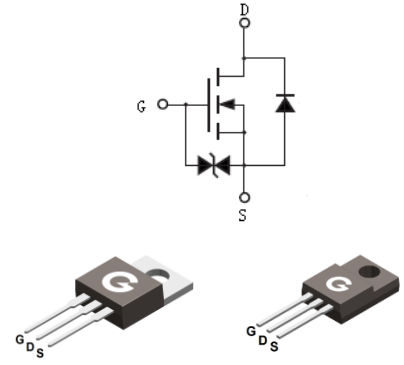
Features

- Low $R_{DS(ON)}$
- Fast switching
- Low gate charge
- Low Reverse transfer capacitances
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: TO-220AB, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208



TO-220AB

ITO-220AB

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL9N90K	TO-220AB	50 pcs / Tube	9N90K
BL9N90KF	ITO-220AB	50 pcs / Tube	9N90KF

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	900	V
Gate-to-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)	I_D	9	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$)	I_D	5.7	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_C = 25^\circ\text{C}$)	I_{DM}	36	A
Single Pulse Avalanche Energy ²	E_{AS}	500	mJ
Power Dissipation (TO-220AB, $T_C = 25^\circ\text{C}$)	P_D	250	W
Power Dissipation (ITO-220AB, $T_C = 25^\circ\text{C}$)		42	W
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case (TO-220AB)	$R_{\theta JC}$	-	-	0.5	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case (ITO-220AB)		-	-	3	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air (TO-220AB)	$R_{\theta JA}$	-	-	50	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air (ITO-220AB)		-	-	62.5	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	900	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900V, V_{GS} = 0V$	-	-	25	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 10	μA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *1	$V_{GS} = 10V, I_D = 4.5A$	-	-	1.1	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	-	4	V
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	2716	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 25V$	-	211	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 1MHz$	-	11	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *3	$V_{DD} = 450V$ $I_D = 9A$ $R_G = 10\Omega$	-	30.4	-	ns
t_r	Turn-on Rise Time *3		-	41.6	-	
$t_{d(OFF)}$	Turn-Off Delay Time *3		-	82	-	
t_f	Turn-Off Fall Time *3		-	52	-	
Q_G	Total Gate-Charge	$V_{DD} = 720V$	-	58	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	10.6	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 9A$	-	23.4	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *1	$I_{SD} = 9A, V_{GS} = 0V$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 9A, V_{GS} = 0V$	-	845	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt = 100A/\mu s$	-	8	-	μC

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100V, V_{GS} = 10V, L = 50mH$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

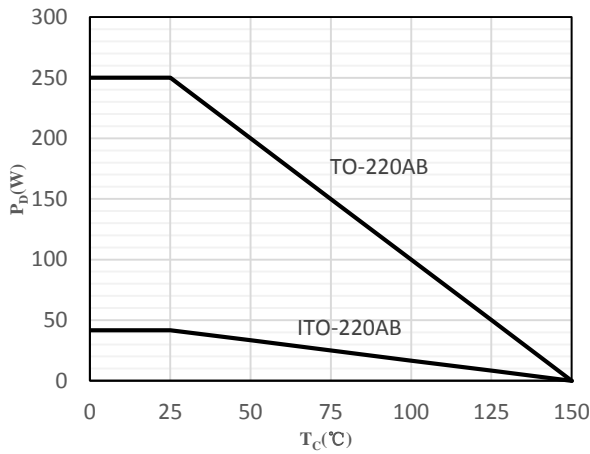


Fig 1 Power Dissipation

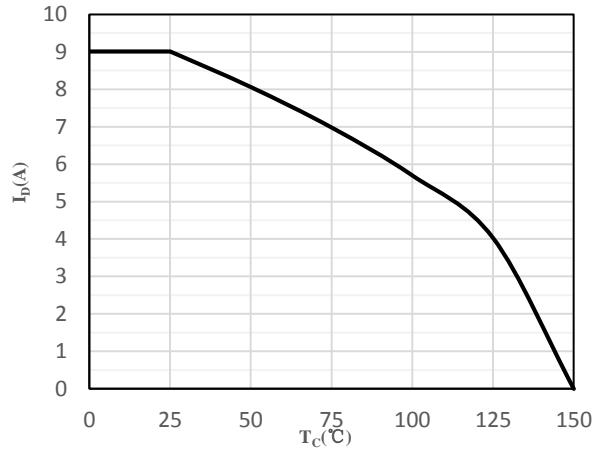


Fig 2 Drain Current

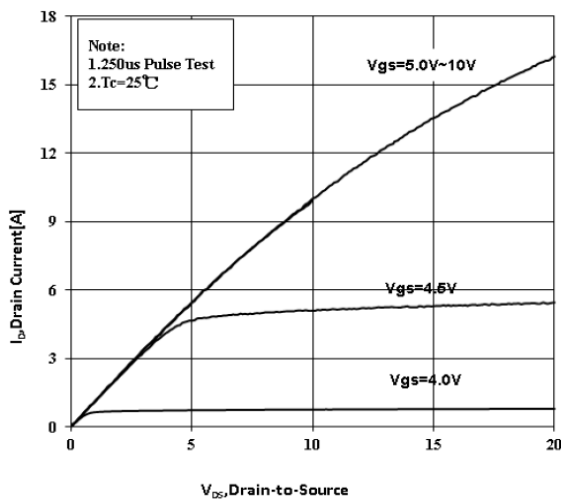


Fig 3 Typical Output Characteristics

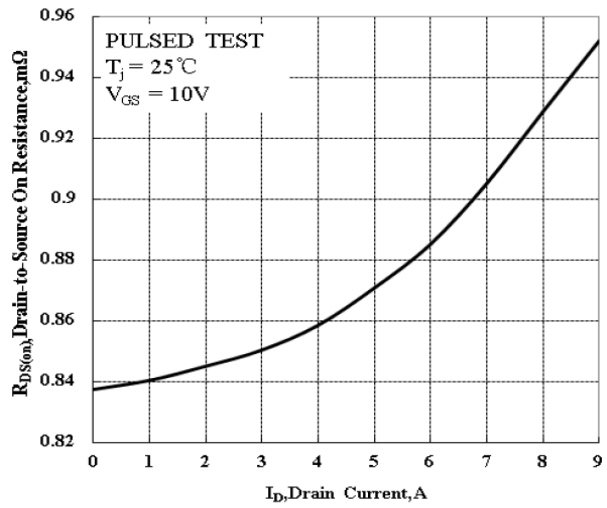


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

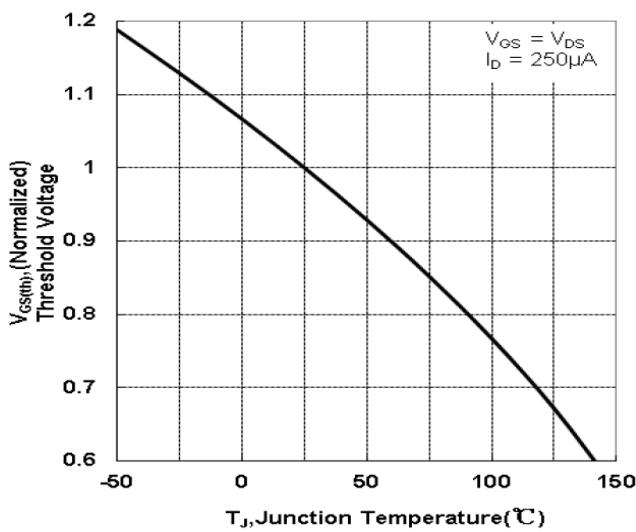


Fig 5 Normalized $V_{GS(th)}$ vs. Junction Temperature

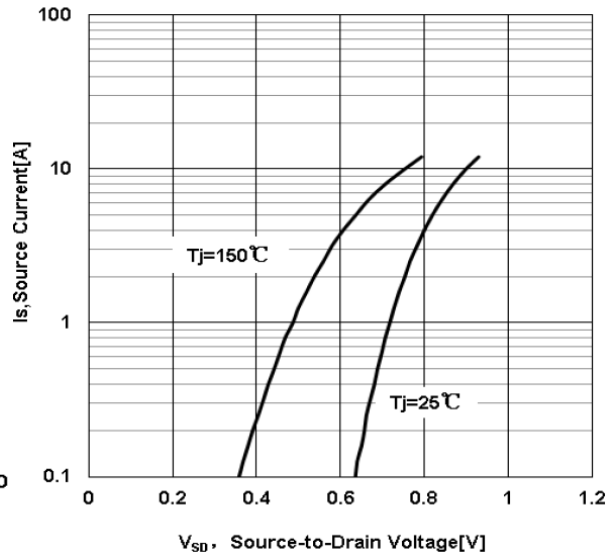


Fig 6 Body-Diode Characteristics

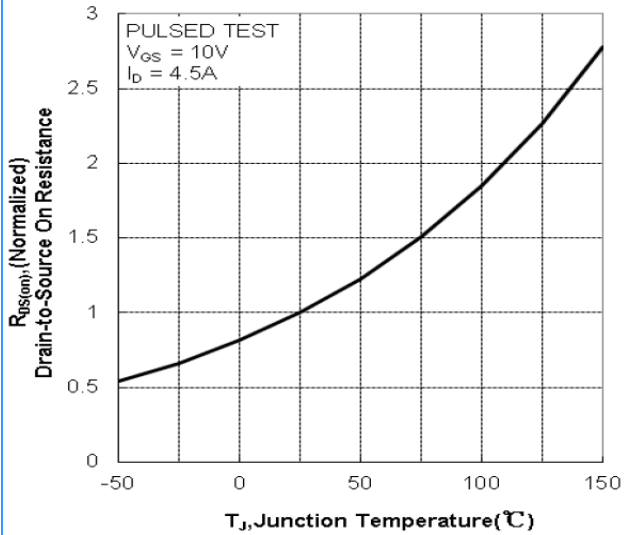


Fig 7 Normalized On-Resistance vs. Junction

Temperature

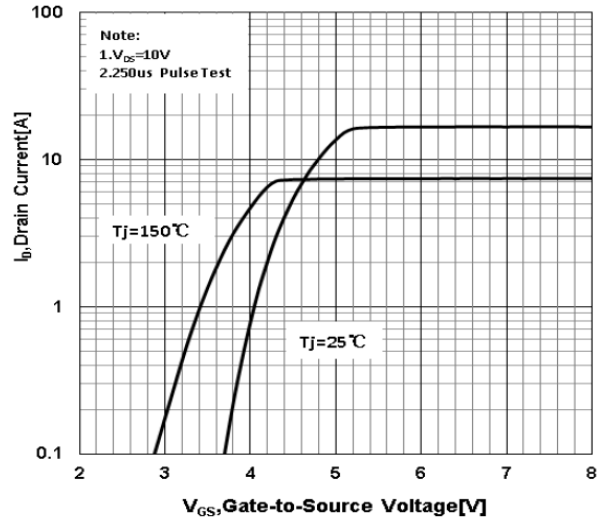


Fig 8 Transfer Characteristics

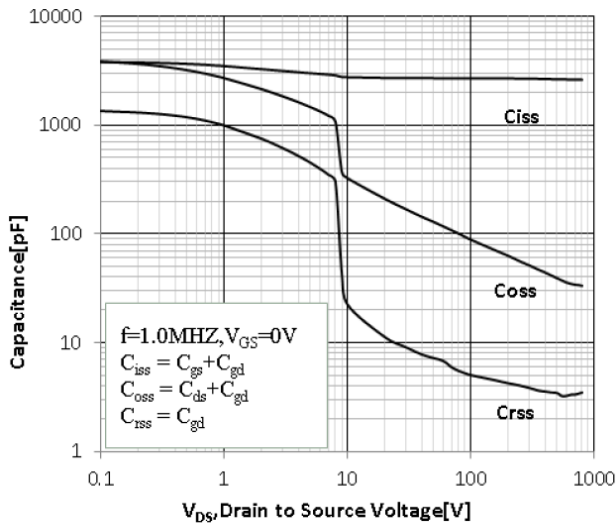


Fig 9 Capacitance Characteristics

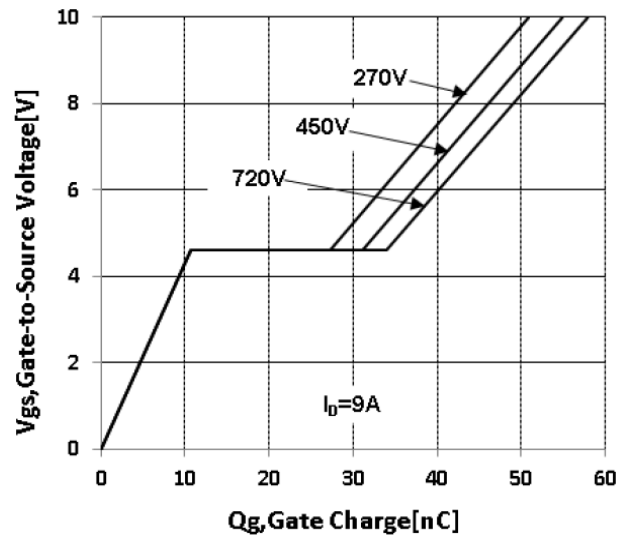


Fig 10 Gate-Charge Characteristics

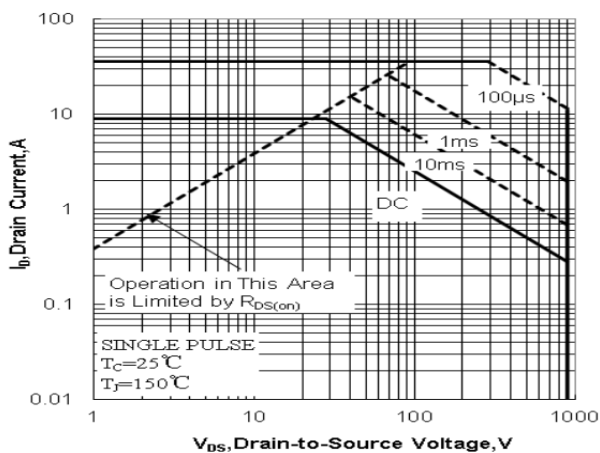


Fig 11 Safe Operation Area (TO-220AB)

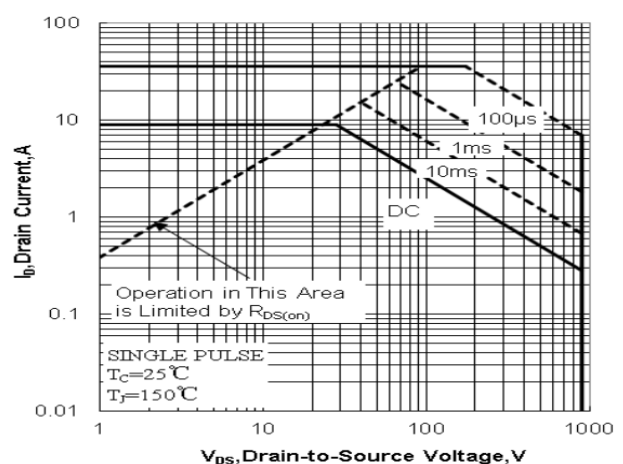


Fig 12 Safe Operation Area (ITO-220AB)

Package Outline Dimensions (Unit: mm)

